

N-Channel 200-V (D-S) MOSFET

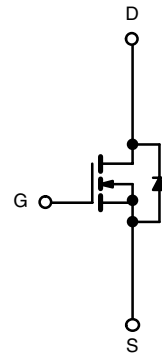
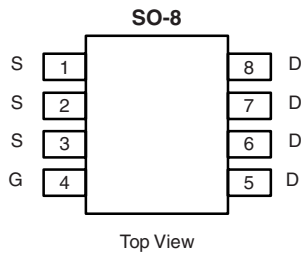
PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
200	0.065 at V _{GS} = 10 V	5.2
	0.072 at V _{GS} = 6.0 V	4.1

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	V _{DS}	200		V	
Gate-Source Voltage	V _{GS}	± 20			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	5.2	3.35	A
		T _A = 70 °C	4.6	2.7	
Pulsed Drain Current	I _{DM}	40			
Avalanch Current	I _{AS}	15			
Continuous Source Current (Diode Conduction) ^a	I _S	2.6	1.3		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	3.1	1.56	W
		T _A = 70 °C	2.0	1.0	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 10 s	33	40	°C/W
		Steady State	65	80	
Maximum Junction-to-Foot (Drain)	R _{thJF}	17	21		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

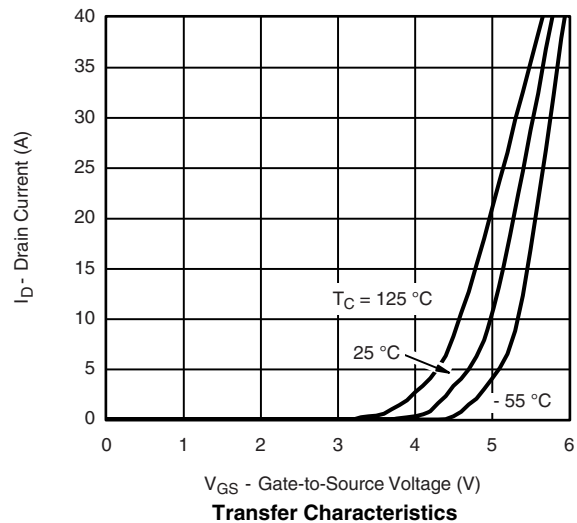
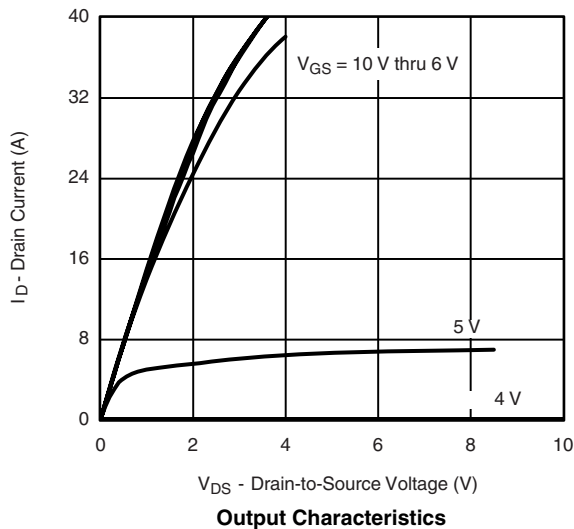
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 160\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 160\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	40			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 4.0\text{ A}$		0.065		Ω
		$V_{GS} = 6.0\text{ V}, I_D = 4.0\text{ A}$		0.072		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 5\text{ A}$		19		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.8\text{ A}, V_{GS} = 0\text{ V}$		0.75	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 4.0\text{ A}$		34	42	nC
Gate-Source Charge	Q_{gs}			7.5		
Gate-Drain Charge	Q_{gd}			12.0		
Gate Resistance	R_g		0.2	0.85	1.3	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\text{ V}, R_L = 25\text{ }\Omega$ $I_D \cong 4.0\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		14	20	ns
Rise Time	t_r			20	30	
Turn-Off Delay Time	$t_{d(off)}$			32	50	
Fall Time	t_f			25	35	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		70	100	

Notes:

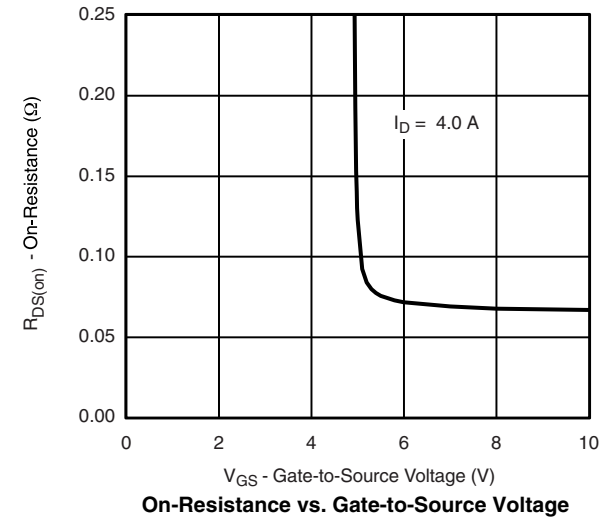
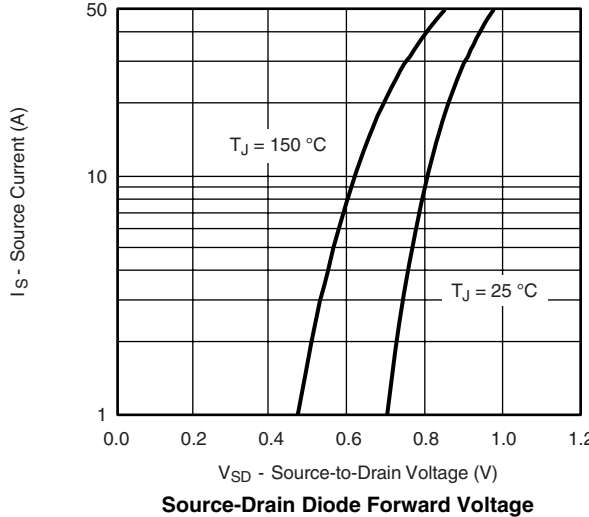
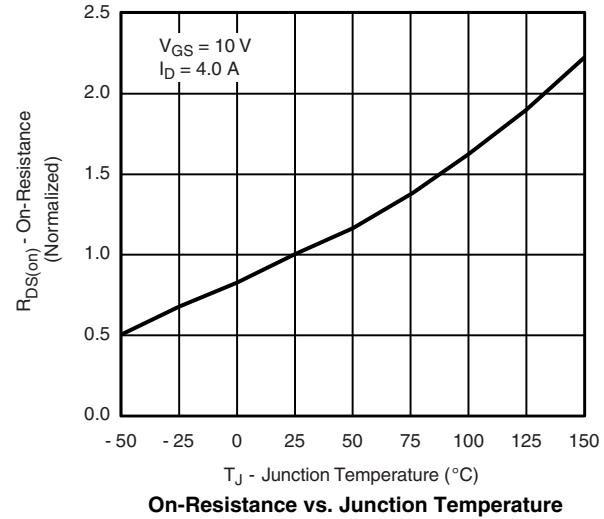
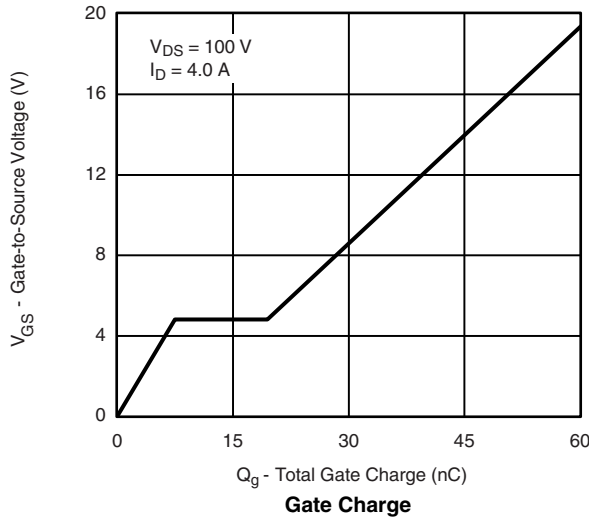
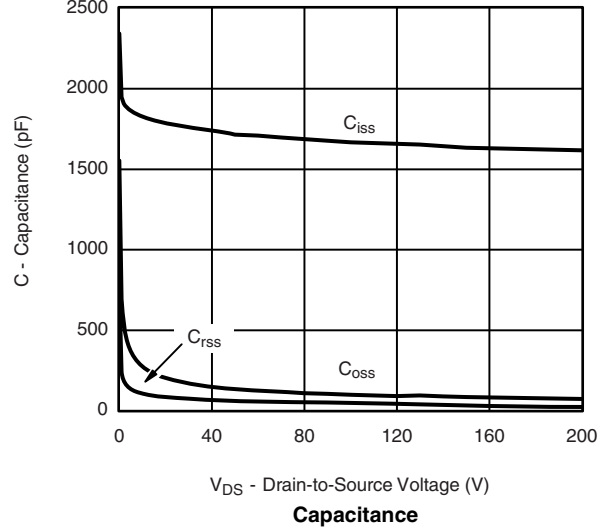
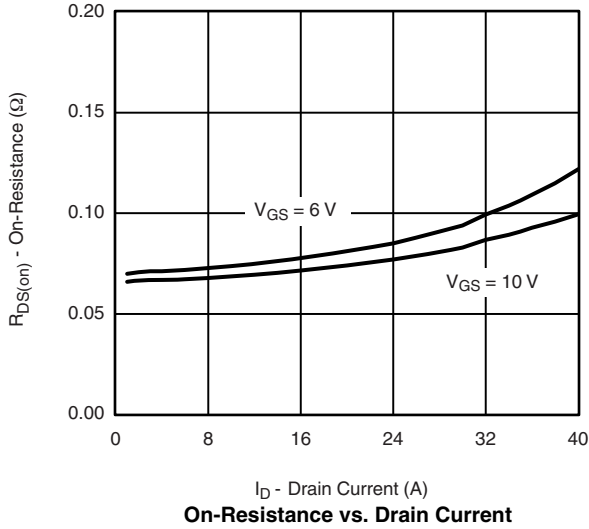
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

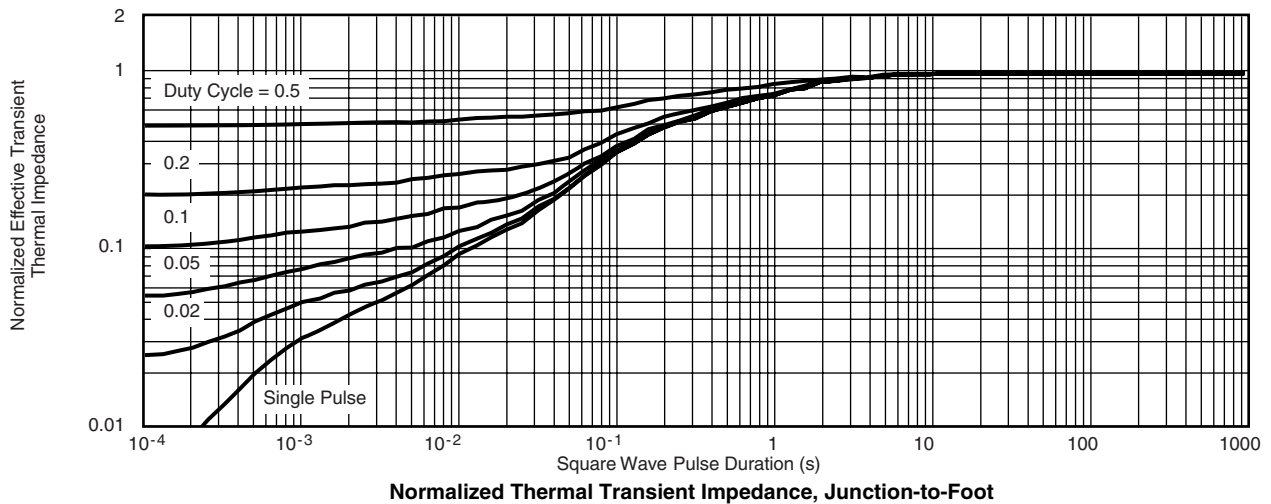
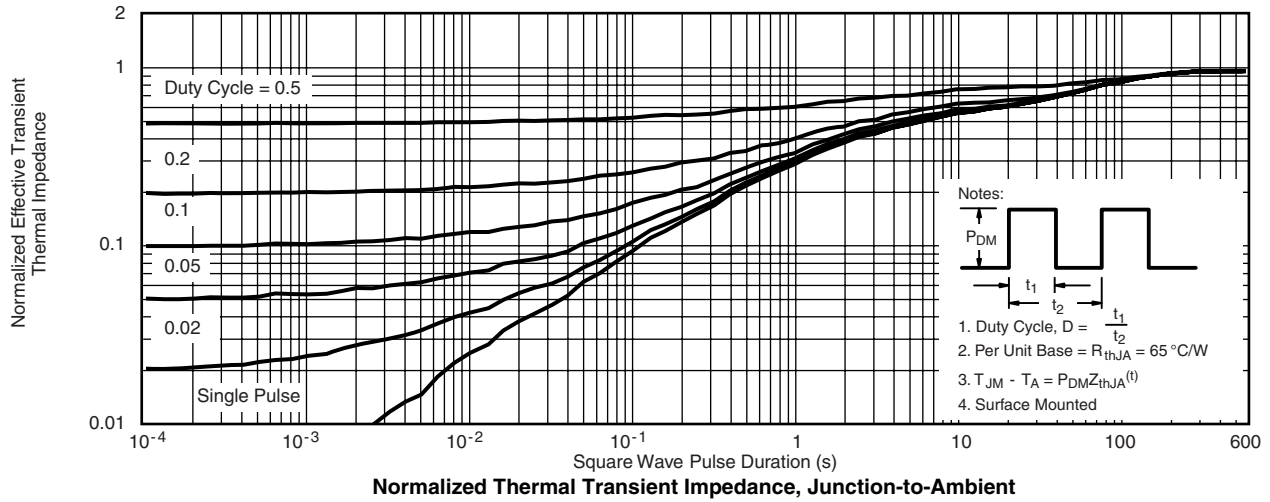
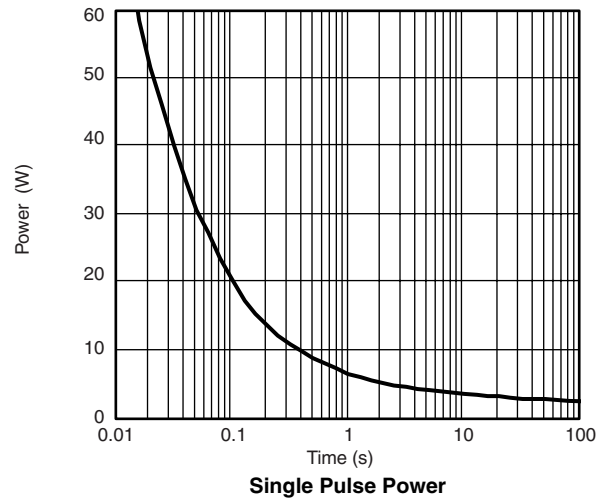
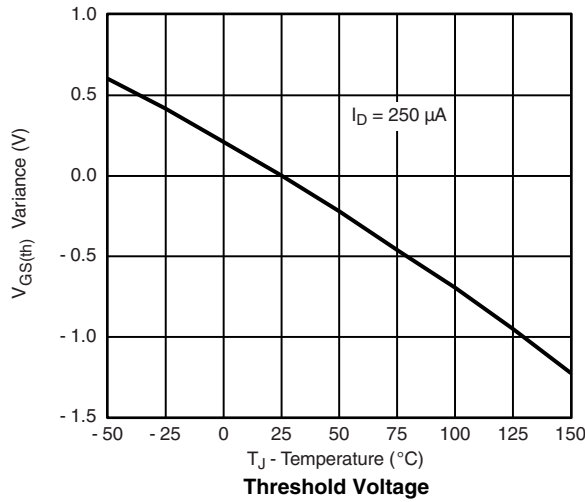
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



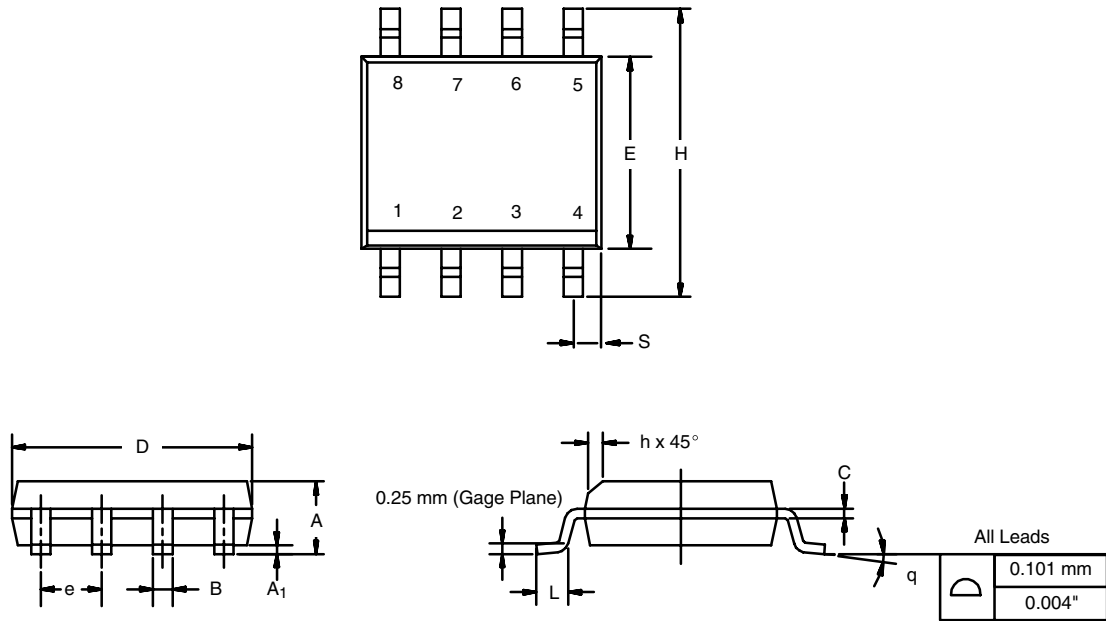
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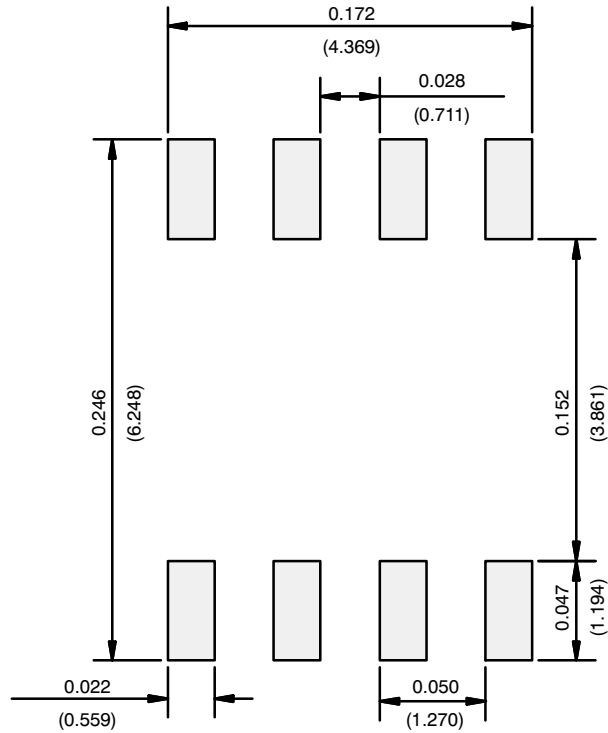


SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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